

GaAs LIGHT-EMITTING DIODE "PILL PACK" 62000 (TYPE GS 1140)



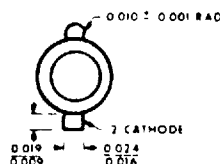
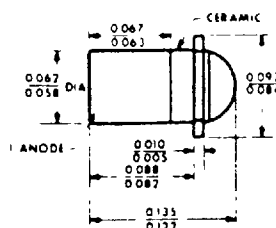
* HIGH INTENSITY GaAlAs VERSIONS AVAILABLE

T-41-11

MINIATURE HIGH EFFICIENCY LED
GLASS/CERAMIC/KOVAR HERMETIC PACKAGE

Mii 62000 is a P-N GaAs Infrared Light Emitting Diode in a package designed to be mounted in a double-clad printed circuit board. It is spectrally and mechanically matched to companion phototransistors and photodarlingtons and is lensed to provide good light transfer and to minimize crosstalk. Available screened to MIL-S-19500.

PHYSICAL DESCRIPTION



ALL DIMENSIONS ARE IN INCHES



OPTICAL/ELECTRICAL CHARACTERISTICS AT 25°C

PARAMETER	OPTICAL POWER		FORWARD DROP	REVERSE BREAKDOWN	RADIATION RISE TIME	PEAK WAVELENGTH	BEAM ANGLE	FWD CURRENT CONTINUOUS
TEST CONDITION	$I_F = 50 \text{ mA}$		$I_F = 50 \text{ mA}$	$I_R = 10 \mu\text{A}$		$I_F = 50 \text{ mA}$	Note 1	25°C Case
SYMBOL	P_o		V_F	BV_R	t_r	λ_P	θ	I_F
UNIT	mW		VOLTS	VOLTS	μsec	nm	degrees	mA
	MIN	TYP	MAX	MIN	TYP	TYP	TYP	MAX
GS 1140-1	0.25	0.30	1.6	2.0	0.7	940	20	100
GS 1140-2	0.40	0.65	1.6	2.0	0.7	940	20	100
GS 1140-3	1.00	1.20	1.6	2.0	0.7	940	20	100
GS 1140-4	1.50	1.60	1.6	2.0	0.7	940	20	100

STD domed lens angle between halfintensity points
Low profile point = 40°

* Contact factory for 62005

Ga As LIGHT-EMITTING DIODE, TYPE GS 1140, *Continued*

62000 LIGHT EMITTING DIODE

ABSOLUTE MAXIMUM RATINGS 25°C FREE AIR TEMPERATURE UNLESS NOTED

Reverse Voltage at 25°C Case Temperature	2 V
Continuous Forward Current at 25°C Case Temperature (See Note)	100 mA
Operating Case Temperature Range	-65°C to 125°C
Storage Temperature Range	-65°C to 150°C
Soldering Temperature (3 Minutes)	240°C

NOTE: Derate linearly to 125°C free-air temperature at the rate of 1 mA/°C.

TYPICAL CHARACTERISTICS

